



#### **40V PNP SMALL SIGNAL TRANSISTOR IN DFN1006**

#### **Features**

- BV<sub>CEO</sub> > -40V
- I<sub>C</sub> = -200mA High Collector Current
- P<sub>D</sub> = 1000mW Power Dissipation
- 0.60mm<sup>2</sup> Package Footprint, 13 times Smaller than SOT23
- 0.5mm Height Package Minimizing Off-Board Profile
- Complementary NPN Type MMBT3904LP
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

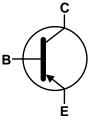
### **Mechanical Data**

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu,
  Solderable per MIL-STD-202, Method 208@4
- Weight: 0.0008 grams (Approximate)

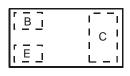
X1-DFN1006-3







Device Symbol



Top View Device Schematic

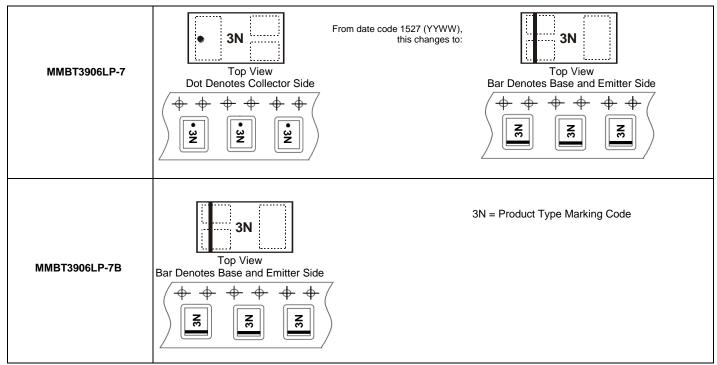
#### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3906LP-7	3N	7	8	3,000
MMBT3906LP-7B	3N	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**





# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-40	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6.0	V
Collector Current	Ic	-200	mA
Peak Collector Current	I <sub>CM</sub>	-200	mA

## Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	400	- mW	
Fower Dissipation	(Note 6)	P <sub>D</sub>	1000		
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)		120	C/VV	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

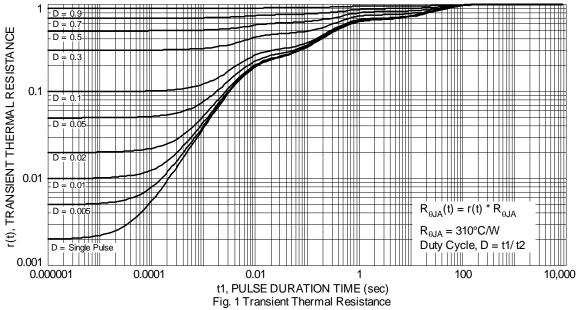
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

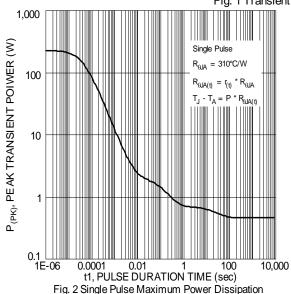
Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics**





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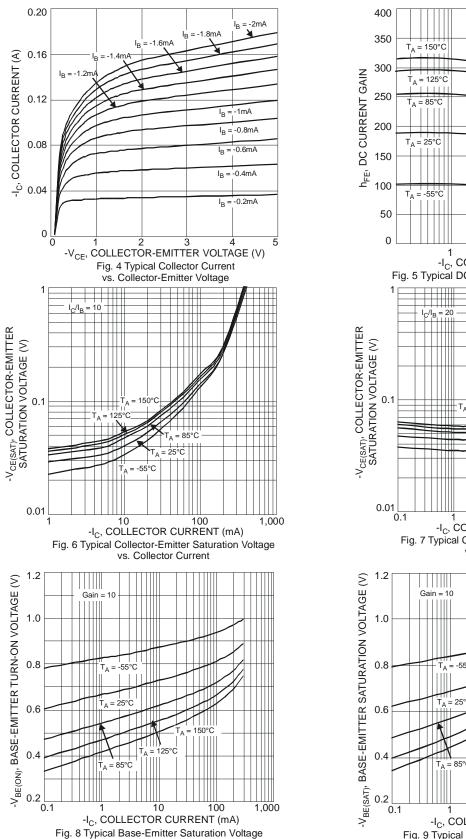
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-40	_	V	$I_C = -100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-40	_	V	$I_C = -10.0$ mA, $I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6.0	_	V	$I_E = -100\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CEX</sub>	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
Collector Cuton Current	I <sub>CBO</sub>		-50	nA	$V_{CB} = -30V, I_E = 0$
Base Cutoff Current	$I_{BL}$	_	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3.0V$
ON CHARACTERISTICS (Note 9)					
		60	_		$I_C = -100\mu A$ , $V_{CE} = -1.0V$
		80	_		$I_C = -1.0 \text{mA}, V_{CE} = -1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	300		$I_C = -10 \text{mA}, V_{CE} = -1.0 \text{V}$
		60	_		$I_C = -50 \text{mA}, V_{CE} = -1.0 \text{V}$
		30	_		$I_C = -100 \text{mA}, V_{CE} = -1.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		-0.25	٧	$I_C = -10mA$ , $I_B = -1.0mA$
Collector-Emitter Saturation Voltage			-0.40		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	-0.65	-0.85	V	$I_C = -10 \text{mA}, I_B = -1.0 \text{mA}$
· ·			-0.95		$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS			,		
Output Capacitance	Cobo	_	4.5	pF	$V_{CB} = -5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	$C_{ibo}$	_	10	pF	$V_{EB} = -0.5V$ , $f = 1.0MHz$ , $I_C = 0$
Input Impedance	h <sub>ie</sub>	2.0	12	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.1	10	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz
Output Admittance	h <sub>oe</sub>	3.0	60	μS	
Current Gain-Bandwidth Product	f <sub>T</sub>	300	_	MHz	$V_{CE} = -20V, I_{C} = -10mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	_	35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	tf	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



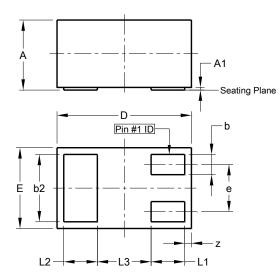
vs. Collector Current

vs. Collector Current



### **Package Outline Dimensions**

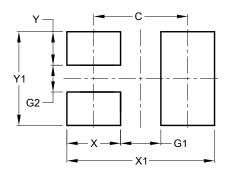
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Х	X1-DFN1006-3					
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0.00	0.05	0.03			
b	0.10	0.20	0.15			
b2	0.45	0.55	0.50			
D	0.95	1.075	1.00			
E	0.55	0.675	0.60			
е	ı	-	0.35			
L1	0.20	0.30	0.25			
L2	0.20	0.30	0.25			
L3	-	-	0.40			
Z	0.02	0.08	0.05			
All D	All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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